

BGA2818 MMIC wideband amplifier Rev. 7 — 30 March 2017

Product data sheet

Product profile 1.

1.1 General description

Silicon Monolithic Microwave Integrated Circuit (MMIC) wideband amplifier with internal matching circuit in a 6-pin SOT363 plastic SMD package.

1.2 Features and benefits

- Internally matched to 50 Ω
- A gain of 30.0 dB at 2150 MHz
- Output power at 1 dB gain compression = 4 dBm at 2150 MHz
- Supply current = 19.9 mA at a supply voltage of 3.3 V
- Reverse isolation > 36 dB up to 2150 MHz
- Good linearity with low second order and third order products
- Noise figure = 3.3 dB at 950 MHz
- Unconditionally stable (K > 1)
- No output inductor required

1.3 Applications

- LNB IF amplifiers
- General purpose low noise wideband amplifier for frequencies between DC and 2.2 GHz

Pinning information 2.

Pin	Description	Simplified outline	Graphic symbol
1	V _{CC}		
2, 5	GND2		
3	RF_OUT		6
4	GND1		
6	RF_IN		4 2, 5 777 777 sym052



3. Ordering information

Table 2. Ordering information									
Type number Package									
	Name	Description	Version						
BGA2818	-	plastic surface-mounted package; 6 leads	SOT363						

4. Marking

Table 3. Marking							
Type number	Marking code	Description					
BGA2818	TA*	* = - : made in Hong Kong					
		* = p : made in Hong Kong					
		* = W : made in China					
		* = t : made in Malaysia					

5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage	RF input AC coupled	-0.5	+5.0	V
I _{CC}	supply current		-	55	mA
P _{tot}	total power dissipation	T _{sp} = 90 °C	-	200	mW
T _{stg}	storage temperature		-40	+125	°C
Tj	junction temperature		-	125	°C
P _{drive}	drive power		-	10	dBm

6. Thermal characteristics

Table 5.	Thermal characteristics			
Symbol	Parameter	Conditions	Тур	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	$P_{tot} = 200 \text{ mW}; T_{sp} = 90 ^{\circ}\text{C}$	300	K/W

7. Characteristics

Table 6.Characteristics

 $V_{CC} = 3.3 V; Z_S = Z_L = 50 \Omega; P_i = -40 \text{ dBm}; T_{amb} = 25 \text{ °C}; \text{ measured on demo board; unless otherwise specified.}$

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CC}	supply voltage		3.0	3.3	3.6	V
I _{CC}	supply current		16.9	19.9	22.7	mA

BGA2818

Table 6. Characteristics ...continued

 $V_{CC} = 3.3 \text{ V}; Z_S = Z_L = 50 \Omega; P_i = -40 \text{ dBm}; T_{amb} = 25 \text{ °C}; \text{ measured on demo board; unless otherwise specified.}$

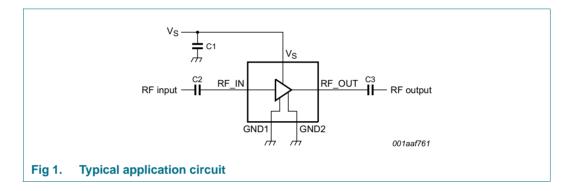
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
G _p	power gain	f = 250 MHz	29.5	30.1	30.7	dB
		f = 950 MHz	29.1	29.8	30.6	dB
		f = 2150 MHz	28.5	30.0	31.4	dB
RL _{in}	input return loss	f = 250 MHz	9	11	-	dB
		f = 950 MHz	10	12	-	dB
		f = 2150 MHz	7	14	-	dB
RL _{out}	output return loss	f = 250 MHz	15	19	-	dB
		f = 950 MHz	14	15	-	dB
		f = 2150 MHz	8	11	-	dB
ISL	isolation	f = 250 MHz	49	70	-	dB
		f = 950 MHz	49	51	-	dB
		f = 2150 MHz	34	36	-	dB
NF	noise figure	f = 250 MHz	-	3.5	4.0	dB
		f = 950 MHz	-	3.3	3.8	dB
		f = 2150 MHz	-	3.3	3.8	dB
B _{-3dB}	-3 dB bandwidth	3 dB below gain at 1 GHz	2.7	2.9	3.1	GHz
К	Rollett stability factor	f = 250 MHz	28	43	-	
		f = 950 MHz	4	5	-	
		f = 2150 MHz	1	1	-	
P _{L(sat)}	saturated output power	f = 250 MHz	9	10	-	dBm
		f = 950 MHz	7	8	-	dBm
		f = 2150 MHz	5	6	-	dBm
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz	7	7	-	dBm
		f = 950 MHz	5	6	-	dBm
		f = 2150 MHz	3	4	-	dBm
IP3 _I	input third-order intercept point	P _{drive} = -43 dBm (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	-13	-11	-	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	-14	-12	-	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	-19	-16	-	dBm
IP3 ₀	output third-order intercept point	P _{drive} = -43 dBm (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	17	19	-	dBm
		f ₁ = 950 MHz; f ₂ = 951 MHz	15	18	-	dBm
		f ₁ = 2150 MHz; f ₂ = 2151 MHz	11	14	-	dBm
P _{L(2H)}	second harmonic output power	P _{drive} = -31 dBm				-
. /		f _{1H} = 250 MHz; f _{2H} = 500 MHz	-	-37	-35	dBm
		f _{1H} = 950 MHz; f _{2H} = 1900 MHz	-	-32	-28	dBm
∆IM2	second-order intermodulation distance	$P_{drive} = -34 \text{ dBm}$ (for each tone)				
		f ₁ = 250 MHz; f ₂ = 251 MHz	35	37	-	dBc
		f ₁ = 950 MHz; f ₂ = 951 MHz	26	32	-	dBc

8. Application information

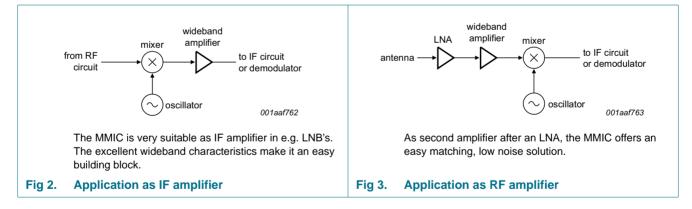
Figure 1 shows a typical application circuit for the BGA2818 MMIC. The device is internally matched to 50 Ω , and therefore does not need any external matching. The value of the input and output DC blocking capacitors C2 and C3 should not be more than 100 pF for applications above 100 MHz. However, when the device is operated below 100 MHz, the capacitor value should be increased.

The 22 nF supply decoupling capacitor C1 should be located as close as possible to the MMIC.

The PCB top ground plane, connected to pins 2, 4 and 5 must be as close as possible to the MMIC, preferably also below the MMIC. When using via holes, use multiple via holes as close as possible to the MMIC.



8.1 Application examples



8.2 Tables

Table 7.Supply current over temperature and supply voltagesTypical values.

Symbol	Parameter	Conditions	T _{amb} (°	T _{amb} (°C)		
			-40	+25	+85	
I _{CC}	supply current	$V_{CC} = 3.0 V$	16.7	16.9	17.2	mA
		$V_{CC} = 3.3 V$	19.7	19.9	20.0	mA
		V _{CC} = 3.6 V	22.6	22.7	22.8	mA

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
P _{L(2H)}	second harmonic output power	f = 250 MHz; P _{drive} = -31 dBm				
		V _{CC} = 3.0 V	-44	-39	-36	dBm
		V _{CC} = 3.3 V	-41	-37	-34	dBm
		V _{CC} = 3.6 V	-39	-36	-32	dBm
		f = 500 MHz; P _{drive} = -31 dBm				
		V _{CC} = 3.0 V	-38	-34	-31	dBm
		V _{CC} = 3.3 V	-35	-32	-29	dBm
		V _{CC} = 3.6 V	-34	-31	-28	dBm

Table 8. Second harmonic output power over temperature and supply voltages Typical values. Second harmonic output power over temperature and supply voltages

Table 9. Input power at 1 dB gain compression over temperature and supply voltages Typical values. Image: Comparison of the supervision over temperature and supply voltages

Symbol	Parameter	Conditions	T _{amb}	(°C)		Unit
			-40	+25	+85	
P _{i(1dB)}	input power at 1 dB gain compression	f = 250 MHz				
		$V_{CC} = 3.0 V$	-22	-22	-22	dBm
		$V_{CC} = 3.3 V$	-22	-22	-22	dBm
		$V_{CC} = 3.6 V$	-21	-21	-22	dBm
		f = 950 MHz				
		$V_{\rm CC} = 3.0 \text{ V}$	-23	-23	-23	dBm
		$V_{CC} = 3.3 V$	-22	-23	-23	dBm
		$V_{CC} = 3.6 V$	-22	-22	-23	dBm
		f = 2150 MHz				
		$V_{CC} = 3.0 V$	-25	-25	-26	dBm
		$V_{CC} = 3.3 V$	-24	-25	-26	dBm
		V _{CC} = 3.6 V	-24	-25	-26	dBm

Symbol	Parameter	Conditions	Tamb	(°C)		Unit
			-40	+25	+85	
P _{L(1dB)}	output power at 1 dB gain compression	f = 250 MHz				
		$V_{CC} = 3.0 V$	6	6	6	dBm
		$V_{CC} = 3.3 V$	8	7	7	dBm
		$V_{CC} = 3.6 V$	9	8	8	dBm
		f = 950 MHz				
		$V_{CC} = 3.0 V$	6	5	4	dBm
		$V_{CC} = 3.3 V$	7	6	5	dBm
		$V_{CC} = 3.6 V$	8	7	6	dBm
		f = 2150 MHz				
		$V_{CC} = 3.0 V$	5	4	2	dBm
		V _{CC} = 3.3 V	6	4	2	dBm
		V _{CC} = 3.6 V	7	5	3	dBm

Table 10. Output power at 1 dB gain compression over temperature and supply voltages Typical values.

Table 11. Saturated output power over temperature and supply voltages Typical values.

Symbol	Parameter	Conditions	T _{amb}	(°C)		Unit
			-40	+25	+85	
P _{L(sat)}	saturated output power	f = 250 MHz				
		$V_{CC} = 3.0 V$	9	9	8	dBm
		V _{CC} = 3.3 V	10	10	9	dBm
		V _{CC} = 3.6 V	11	11	10	dBm
		f = 950 MHz				
		$V_{CC} = 3.0 V$	8	7	7	dBm
		V _{CC} = 3.3 V	9	8	8	dBm
		V _{CC} = 3.6 V	10	9	8	dBm
		f = 2150 MHz				
		$V_{CC} = 3.0 V$	7	6	4	dBm
		$V_{CC} = 3.3 V$	8	6	4	dBm
		V _{CC} = 3.6 V	8	7	5	dBm

Symbol	Parameter	Conditions	Tamb	T _{amb} (°C)		
			-40	+25	+85	
∆IM2 second-order intermodulation distant	second-order intermodulation distance	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -34 \text{ dBm}$				
		V _{CC} = 3.0 V	52	39	33	dBc
		V _{CC} = 3.3 V	45	37	31	dBc
		V _{CC} = 3.6 V	42	35	30	dBc
		f ₁ = 950 MHz; f ₂ = 951 MHz; P _{drive} = -34 dBm				
		V _{CC} = 3.0 V	45	35	29	dBc
		V _{CC} = 3.3 V	40	32	27	dBc
		V _{CC} = 3.6 V	37	31	26	dBc

Table 12. Second-order intermodulation distance over temperature and supply voltages Typical values. Values.

Table 13. Output third-order intercept point over temperature and supply voltages *Typical values.*

Symbol	Parameter	Conditions	T _{amb} (°C)			Unit
			-40	+25	+85	
IP3 ₀	output third-order intercept point	$f_1 = 250 \text{ MHz};$ $f_2 = 251 \text{ MHz};$ $P_{drive} = -43 \text{ dBm}$				
		$V_{CC} = 3.0 V$	18	17	17	dBm
		V _{CC} = 3.3 V	20	19	17	dBm
		V _{CC} = 3.6 V	22	20	18	dBm
		$f_1 = 950 \text{ MHz};$ $f_2 = 951 \text{ MHz};$ $P_{drive} = -43 \text{ dBm}$				
		$V_{CC} = 3.0 V$	18	17	15	dBm
		$V_{CC} = 3.3 V$	19	18	15	dBm
		V _{CC} = 3.6 V	20	18	16	dBm
		$f_1 = 2150 \text{ MHz};$ $f_2 = 2151 \text{ MHz};$ $P_{drive} = -43 \text{ dBm}$				
		$V_{CC} = 3.0 V$	16	14	11	dBm
		V _{CC} = 3.3 V	17	14	11	dBm
		V _{CC} = 3.6 V	17	14	11	dBm

Symbol	Parameter	Conditions	T _{amb} (°	T _{amb} (°C)		
			-40	+25	+85	
B _{-3dB}	-3 dB bandwidth	$V_{CC} = 3.0 V$	2.96	2.88	2.75	GHz
		$V_{CC} = 3.3 V$	2.96	2.86	2.73	GHz
		V _{CC} = 3.6 V	2.95	2.84	2.70	GHz

9. Test information

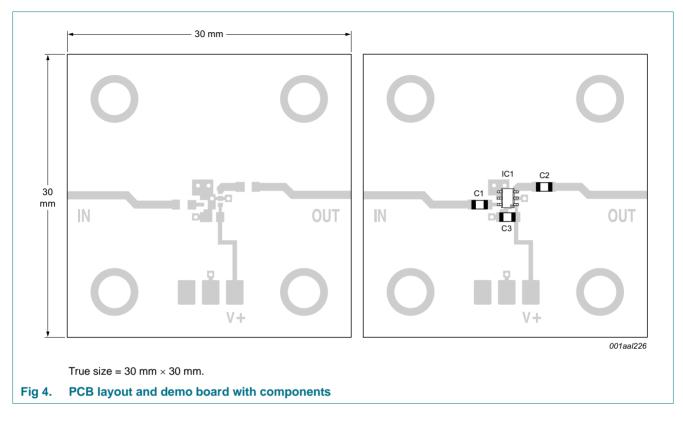


Table 15. List of components used for the typical application

Component	Description	Value	Dimensions
C1, C2	multilayer ceramic chip capacitor	100 pF	0603
C3	multilayer ceramic chip capacitor	22 nF	0603
IC1	BGA2818 MMIC		SOT363

10. Package outline

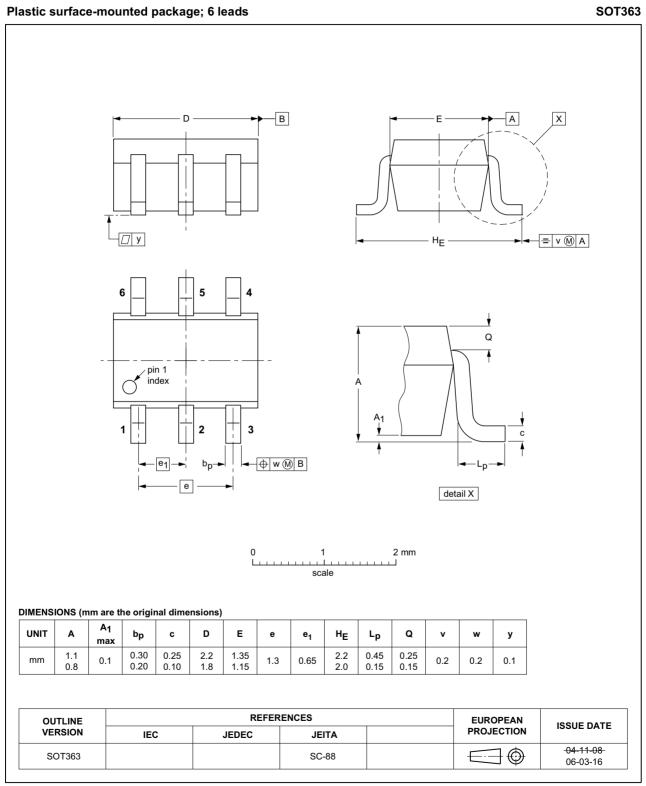


Fig 5. Package outline SOT363

BGA2818 Product data sheet

11. Abbreviations

Table 16. Ab	Table 16. Abbreviations				
Acronym	Description				
IF	Intermediate Frequency				
LNA	Low-Noise Amplifier				
LNB	Low-Noise Block converter				
PCB	Printed-Circuit Board				
SMD	Surface Mounted Device				

12. Revision history

Table 17. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BGA2818 v.7	20170330	Product data sheet	-	BGA2818 v.6		
Modifications:	to -35 dBm	he maximum value for f1		, i i i i i i i i i i i i i i i i i i i		
	 <u>Table 6 on page 2</u>: the maximum value for f1H = 950 MHz; f2H = 1900 MHz has been changed to -28 dBm 					
	 <u>Table 6 on page 2</u>: the minimum value for ∆IM2 (f1 = 250 MHz; f2 = 251 MHz) has been changed to 35 dBc 					
	 <u>Table 6 on page 2</u>: the minimum value for ∆IM2 (f1 = 950 MHz; f2 = 951 MHz) has been changed to 26 dBc 					
	 <u>Table 6 on page 2</u>: the maximum value removed from RL_{in}, RL_{out}, ISL, K, P_{L(sat)}, P_{L(1dB)}, IP3_I, IP3_O, ΔIM2 					
	• <u>Table 6 on page 2</u> : t	he minimum value remov	ed from NF, P _{L(2H)}	1		
DC 40040 v/C	204 0444 5	Draduct data ab act				
BGA2818 v.6	20161115	Product data sheet	-	BGA2818 v.5		
Modifications:	Table 6 on page 2: t	he min/max value for P _{L(2}	_{2H)} (f _{1H} = 950 MHz; f _{2H} = ′	1900 MHz) removed		
	• <u>Table 6 on page 2</u> : t	he min/max value for ΔIM	l2 (f ₁ = 950 MHz; f ₂ = 951	MHz) removed		
BGA2818 v.5	20150206	Product data sheet	-	BGA2818 v.4		
Modifications:	Table 4 on page 2: t	he maximum value for P _d	Irive has been changed to	10 dBm		
BGA2818 v.4	20141209	Product data sheet	-	BGA2818 v.3		
BGA2818 v.3	20130819	Product data sheet	-	BGA2818 v.2		
BGA2818 v.2	20120501	Product data sheet	-	BGA2818 v.1		
BGA2818 v.1	20111220	Product data sheet	-	-		

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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